# Electronimpact excitation diagnostics in pulse-modulated $\mathrm{Ar} / \mathrm{O}_{2}$ inductively coupled plasma 

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An intensified charge-coupled device (ICCD) camera is applied to investigate the electron excitation dynamics of $\operatorname{Ar}\left(2 p_{1}\right.$, with emission line of 750 nm ) in pulse-modulated radio frequency ( rf ) $\mathrm{Ar} / \mathrm{O}_{2}$ inductively coupled plasmas (ICPs). Since the electron impact excitation rate has two excitation maxima within a rf cycle during H-mode in ICPs, whereas only an excitation maximum appears in E-mode, the time of the E-H mode transition and the spatial-temporal distributions of the electron excitation rate during the H -mode and a whole pulse period are investigated in nanosecond resolved pulse-modulated $\mathrm{rf} \mathrm{Ar} / \mathrm{O}_{2}$ ICPs. It is founded that with the increase of the duty cycle/pressure, the time of the E-H mode transition at the initial active glow decreases, while it increases with the source power increasing. Therefore, the capacitive coupling (E-mode) at the initial pulse duration can be weakened by adjusting the discharge parameters. In addition, itis founded that as the $\mathrm{O}_{2}$ content/pressure increases, the distribution of electron impact excitation (within a rf cycle during theH-mode) in $z$-axis concentrates closer to the quartz window. Meanwhile, the bimodal structure of the electron excitation within a rf cycle becomes more prominent at larger $\mathrm{O}_{2}$ content/higher pressure. Besides, it is found that as the pressure/ $\mathrm{O}_{2}$ content increases, the appearance time of the electron excitation maximum at the initial pulse in a whole pulse period is shortened, while it is prolonged with the discharge power increasing.

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